

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listing, of claims in the application:

**Listing of Claims:**

Claim 1 (canceled)

Claim 2 (canceled)

Claim 3 (canceled)

Claim 4 (canceled)

Claim 5 (canceled)

Claim 6 (canceled)

Claim 7 (canceled)

Claim 8 (canceled)

Claim 9 (canceled)

Claim 10 (canceled)

Claim 11 (canceled)

Claim 12 (canceled)

Claim 13 (canceled)

Claim 14 (canceled)

Claim 15 (canceled)

Claim 16 (canceled)

Claim 17 (canceled)

Claim 18 (canceled)

Claim 19 (canceled)

Claim 20 (canceled)

Claim 21 (canceled)

Claim 22 (canceled)

Claim 23 (canceled)

Claim 24 (canceled):

Claim 25 (canceled):

Claim 26 (canceled):

Claim 27 (canceled):

Claim 28 (canceled):

Claim 29 (presently amended): A semiconductor substrate material for producing a semiconductor substrate, the semiconductor substrate material comprising:

a multitude of hollow microspheres, each one of the multitude of hollow microspheres having an inner layer and an outer layer, the inner layer comprising a first material, the outer layer comprising a second material, and the first material and the second material differing from one another, wherein the multitude of hollow microspheres comprises a multitude of gas filled ceramic microspheres

~~The semiconductor substrate material in accordance with claim 25,~~ wherein the second material of the outer layer comprises a glass material, the inner layer of each of the gas filled ceramic microspheres has a first ~~given~~-melting point, the outer layer of the glass material has a second ~~given~~-melting point, and the first ~~given~~-melting point is higher than the second ~~given~~-melting point.

Claim 30 (previously presented): The semiconductor substrate material in accordance with claim 29, wherein the outer layer of glass material of one of the multitude of gas filled ceramic microspheres is sintered to the outer layer of glass material of another one of the multitude of gas filled ceramic microspheres.

Claim 31 (canceled):

Claim 32 (canceled):

Claim 33 (presently amended): The semiconductor substrate material in accordance with claim ~~29~~ 34, wherein a hardened matrix contains the gas filled glass microspheres.

Claim 34 (presently amended): The semiconductor substrate material in accordance with claim ~~34~~ 29, wherein a glaze is disposed on a top surface of the semiconductor

substrate.

Claim 35 (canceled):

Claim 36 (canceled):

Claim 37 (canceled):

Claim 38 (canceled):

Claim 39 (presently amended): The semiconductor substrate material in accordance with claim ~~38~~ 29, wherein the hardened matrix containing the multitude of hollow microspheres comprises glass particles, a binder material, and a viscosity modifier.

Claim 40 (presently amended): The semiconductor substrate material in accordance with claim ~~39~~ 29, wherein the binder material comprises at least one chosen from the group consisting of ethyl cellulose, an acrylic, a polyvinyl alcohol, an organic polymer, and a borophosphate glass.

Claim 41 (presently amended): The semiconductor substrate material in accordance with claim ~~39~~ 29, wherein the at least one viscosity modifier comprises at least one chosen from the group consisting of a surfactant, an organic thickener, a magnesium silicates thickening agent, and a filler material.

Claim 42 (canceled):

Claim 43 (canceled):

Claim 44 (canceled):

Claim 45 (presently amended): The semiconductor substrate material in accordance with claim 24 29, wherein the semiconductor substrate forms a semiconductor wafer.

Claim 46 (presently amended): The semiconductor substrate material in accordance with claim 24 29, wherein the semiconductor substrate forms an integrated circuit die.